

2SC5273

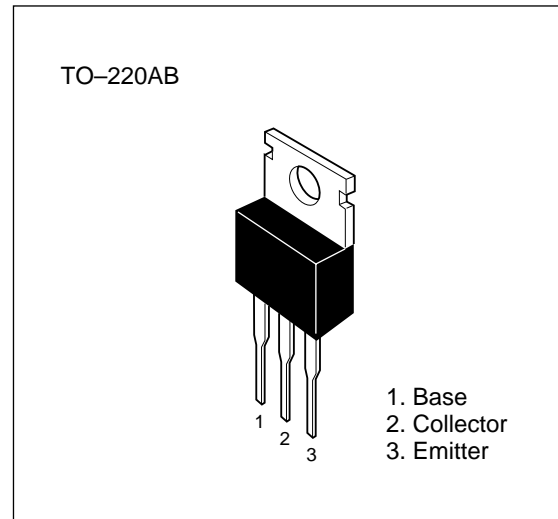
Silicon NPN Triple difused

Application

High voltage amplifier

Features

- High brakedown voltage
 $V_{(BR)CEO} = 1300 \text{ V Min}$



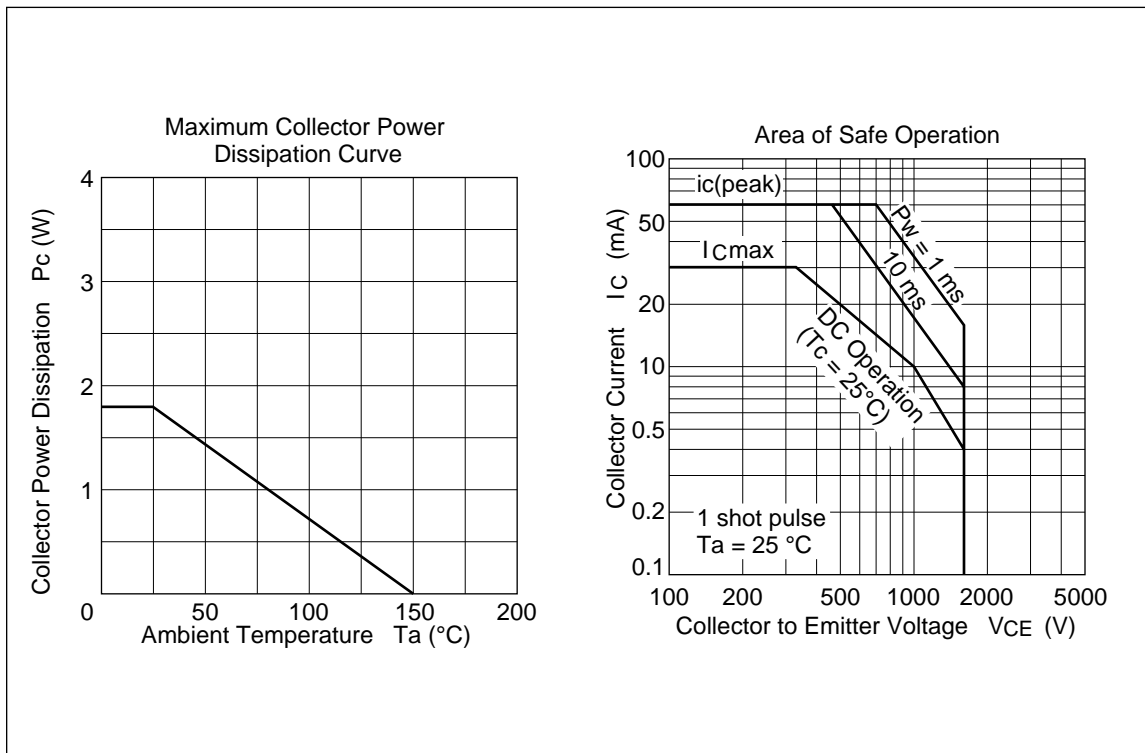
Absolute Maximum Ratings (Ta = 25°C)

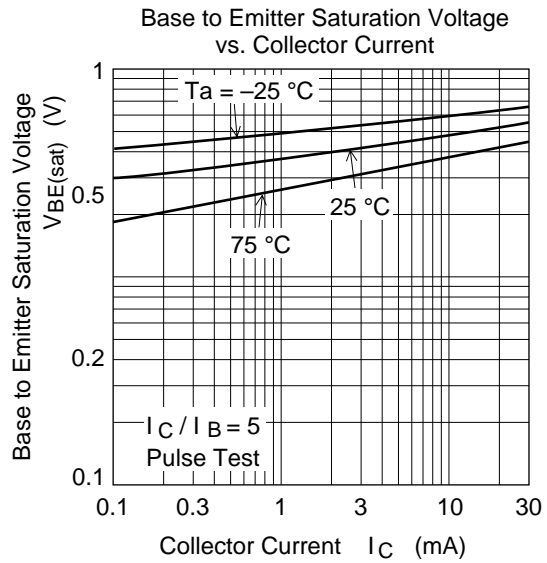
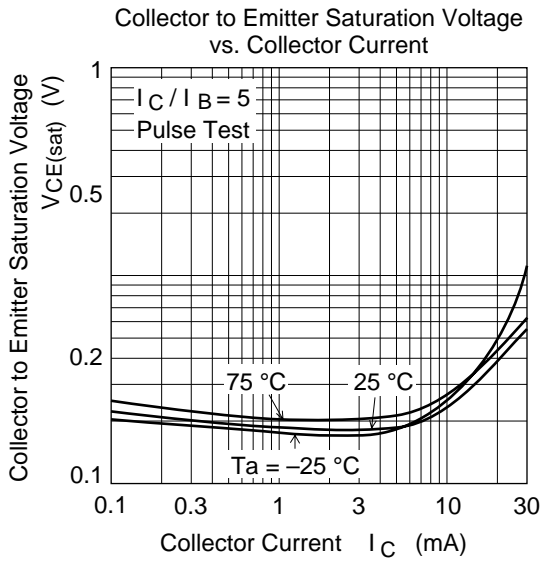
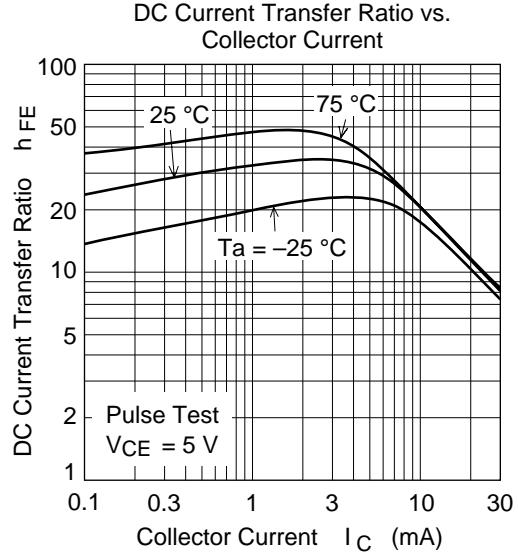
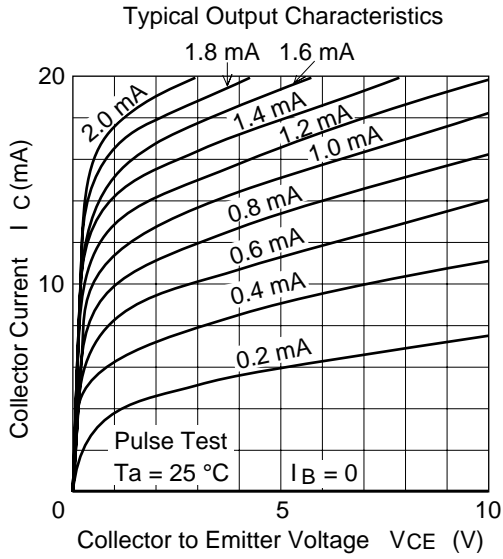
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	1300	V
Collector to emitter voltage	V_{CEO}	1300	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	30	mA
Collector peak current	i_c (peak)	60	mA
Collector power dissipation	P_C	1.8	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

2SC5273

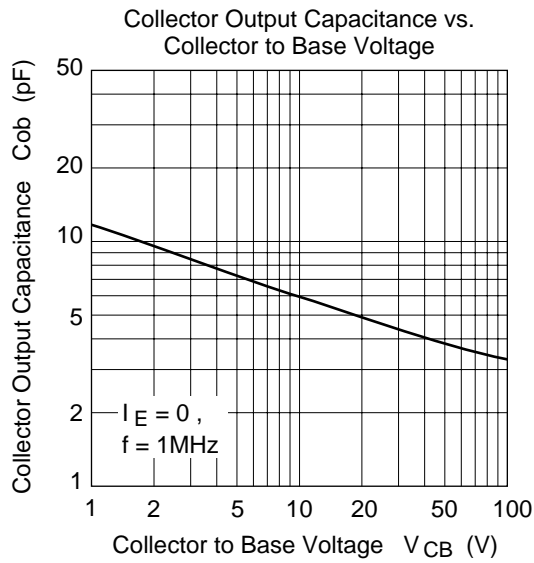
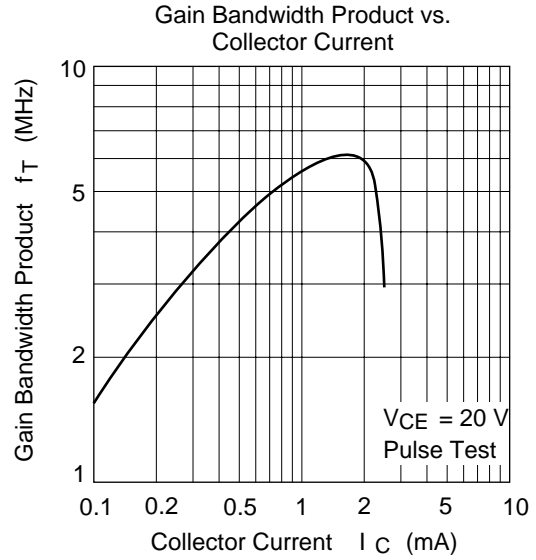
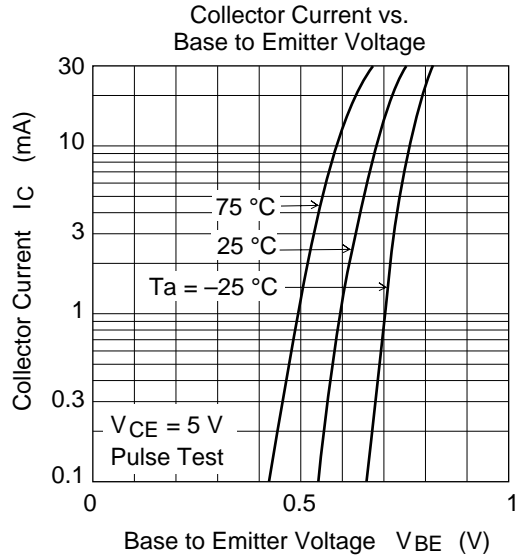
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector cutoff current	I_{CES}	—	—	10	μA	$V_{CE} = 1300\text{ V}$, $R_{BE} = 0$
Collector cutoff current	I_{CEO}	—	—	100	μA	$V_{CE} = 1300\text{ V}$, $R_{BE} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 6\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}	10	—	—		$V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5.0	V	$I_C = 10\text{ mA}$, $I_B = 2\text{ mA}$
Gain bandwidth product	f_T	—	5.5	—	MHz	$V_{CE} = 20\text{ V}$, $I_C = 1\text{ mA}$
Collector output capacitance	C_{ob}	—	3.4	—	pF	$V_{CB} = 100\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$





2SC5273



Package Dimensions

Unit : mm

